

<b>Notice of References Cited</b>	Application/Control No. 09/891,129	Applicant(s)/Patent Under Reexamination NISHIYAMA ET AL.	
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6291867	09-2001	Wallace et al.	257/410
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	A. Chatterjee et al., CMOS Metal Replacement Gate Transistors Using Tantalum Pentaoxide Gate Insulator. IEDM 1998, pp. 777-780.
	V	W. J. Qi et al., MOSCAP and MOSFET Characteristics Using ZrO <sub>2</sub> Gate Dielectric Deposited Directly on Si. IEDM 1999, pp. 145-148.
	W	S. Inumiya et al., Conformable Formation of High Quality Ultra-Thin Amorphous Ta <sub>2</sub> O <sub>5</sub> Gate Dielectrics Utilizing Water Assisted Deposition (WAD) for Sub 50 nm Damascene Metal Gate MOSFETs. IEDM 2000, pp. 649-652.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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